EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/709603	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:27
L2	38	(silicon adj nitride adj read adj only adj memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:04
L3	0	(silicon adj nitride adj read adj only adj memory) and plasma and treatment and test and inspection and wafer and quality and conrol and alloy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:29
L4	1	(silicon adj nitride adj read adj only adj memory) and plasma and treatment and test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:56
L5	1	(silicon adj nitride adj read adj only adj memory) and (plasma adj treatment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L6	0	(silicon adj nitride adj read adj only adj memory) and (plasma adj treat)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L7	0	(silicon adj nitride adj read adj only adj memory) and (plasma adj treating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:33
L8	2	(silicon adj nitride adj read adj only adj memory)and plasma and test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:35

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L9	7	(silicon adj nitride adj read adj only adj memory)and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:36
L10	7	9 and (test or plasma or treat or treatment or etch or control or quality or inspection or alloy or allyoing or process or sort or cell or retention or capacity or heat or heating or baking or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:05
L11	1	(silicon adj nitride adj read adj only adj memory) and (cell adj retention adj capacity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:55
L12	0	(silicon adj nitride adj read adj only adj memory) and plasma and treat	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 14:56
L13	1	"6437398".PN.	USPAT; USOCR	OR	ON	2006/03/16 15:01
L14	4	(silicon adj nitride adj read adj only adj memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:05
L15	4	14 and (test or plasma or treat or treatment or etch or control or quality or inspection or alloy or allyoing or process or sort or cell or retention or capacity or heat or heating or baking or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L16	513	438/9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L17	3687	438/14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10

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L18	645	438/263	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L19	1590	438/264	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L20	2696	438/238	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L21	1519	438/381	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:10
L22	1961	438/745	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:11
L23	1735	438/723	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:11
L24	503	438/798	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:11
L25	286	438/513	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:11
L26	1	("6869844").PN.	USPAT	OR	OFF	2006/03/16 15:11
L27	1	("6881619").PN.	USPAT	OR	OFF	2006/03/16 15:11

L28	1	("6580630").PN.	USPAT	OR	OFF	2006/03/16 15:11
L29	1	("6469342").PN.	USPAT	OR	OFF	2006/03/16 15:12
L30	1	(memory adj cell adj retention adj check)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/16 15:18